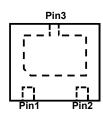




VCTU12V1K17P

Description

The VCTU12V1K17P transient voltage suppressor is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The VCTU12V1K17P protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The VCTU12V1K17P is available in a DFN2×2-3L package with working voltages of 12 volt.



Pin configuration

Feature

- > 4500W Peak pulse power per line (t_P = 8/20µs)
- DFN2×2-3L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- Low clamping Voltage
- > RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 80A (5/50ns), IEC 61000-4-5 (Lightning) 200A (8/20us)

Pin 1,2 OPin 3 Circuit Diagram

Applications

- > Cell phone handsets and accessories
- > Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

T12 •003

Marking (Top View)

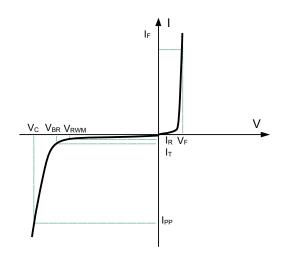
Mechanical Characteristics

- ➤ Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- ➤ Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- ➤ Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil



Electronics Parameter

| Symbol | Parameter | | |
|------------------|--|--|--|
| V _{RWM} | Peak Reverse Working Voltage | | |
| I _R | Reverse Leakage Current @ V _{RWM} | | |
| V_{BR} | Breakdown Voltage @ I _⊤ | | |
| Ι _Τ | Test Current | | |
| I _{PP} | Maximum Reverse Peak Pulse Current | | |
| Vc | Clamping Voltage @ IPP | | |
| P _{PP} | Peak Pulse Power | | |
| CJ | Junction Capacitance | | |
| I _F | Forward Current | | |
| V _F | Forward Voltage @ I _F | | |



Electrical characteristics per line@25℃(unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Units |
|------------------------------|------------------|--|------|------|------|-------|
| Peak Reverse Working Voltage | V _{RWM} | | | | 12 | V |
| Breakdown Voltage | V _{BR} | I _t =1mA | 14 | 14.5 | | V |
| Reverse Leakage Current | I _R | V _{RWM} =12V | | | 1 | μA |
| Maximum Reverse Peak Pulse | I _{PP} | | | 200 | | Α |
| Current Clamping Voltage | Vc | I _{PP} =40A t _P = 8/20μs | | 16 | 18 | V |
| Clamping Voltage | Vc | I _{PP} =90A t _P = 8/20μs | | 18 | 20 | ٧ |
| Clamping Voltage | Vc | I _{PP} =140A t _P = 8/20μs | | 20.5 | 24 | V |
| Clamping Voltage | Vc | I _{PP} =185 A t _P = 8/20µs | | 25 | 30 | V |
| Junction Capacitance | C _j | V _R =0V f = 1MHz | | 1000 | 1500 | pF |

Absolute maximum rating@25℃

| Rating | Symbol | Value | Units |
|--|------------------|--------------|------------|
| Peak Pulse Power (t _P = 8/20μS) | P _{pp} | 4500 | W |
| Lead Soldering Temperature | T∟ | 260 (10 sec) | °C |
| Operating Temperature | TJ | -55 to 150 | $^{\circ}$ |
| Storage Temperature | T _{STG} | -55 to 150 | °C |



上海为芯电子科技有限公司

Typical Characteristics

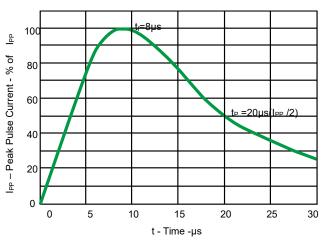


Fig 1.Pulse Waveform

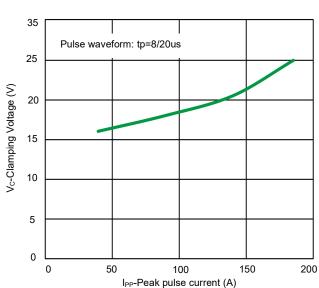


Fig 3. Clamping voltage vs. Peak pulse current

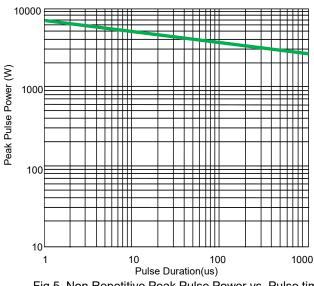


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

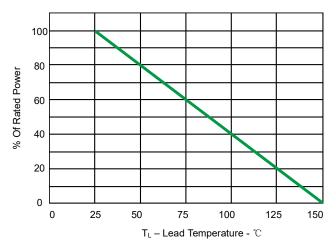


Fig 2.Power Derating Curve

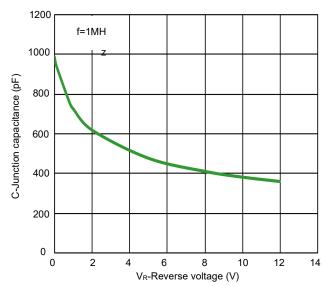
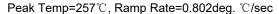


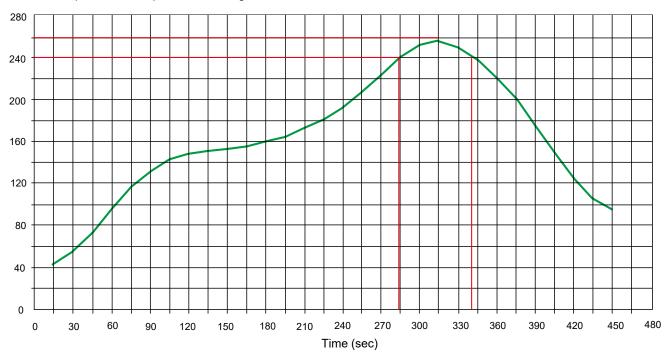
Fig 4. Capacitance vs. Reveres voltage





Solder Reflow Recommendation





PCB Design

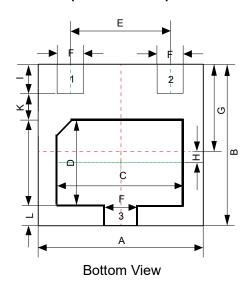
For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- > Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- > Do not make false economies and save copper for the ground connection.
- > Place via holes to ground as close as possible to the anode of the TVS diode.
- Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.



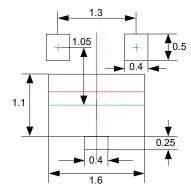


Product dimension (DFN2×2-3L)





| Dim | Millimeters | | |
|-----|-------------|------|--|
| | MIN | MAX | |
| Α | 1.90 | 2.10 | |
| В | 1.90 | 2.10 | |
| С | 1.40 | 1.60 | |
| D | 0.90 | 1.15 | |
| E | 1.30BSC | | |
| F | 0.25 | 0.40 | |
| G | 0.90 | 1.10 | |
| Н | 0.20 | 0.30 | |
| I | 0.32 | 0.48 | |
| J | 0.50 | 0.65 | |
| К | 0.20 | 0.45 | |
| L | 0.15 | 0.30 | |



Unit:mm

Recommended Soldering Pad

Ordering information

| Device | Package | Reel | Shipping |
|--------------|---------------------|------|--------------------|
| VCTU12V1K17P | DFN2×2-3L (Pb-Free) | 7" | 3000 / Tape & Reel |



Important Notice and Disclaimer

Weforsemi reserves the right to make changes to this document and its products and specifications at any time without notice. Customers should obtain and confirm the latest product information and specifications before final design, purchase or use.

Weforsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Weforsemi assume any liability for application assistance or customer product design. Weforsemi does not warrant or accept any liability with products which are purchased or used for any unintended or unauthorized application.

No license is granted by implication or otherwise under any intellectual property rights of Weforsemi .

Weforsemi products are not authorized for use as critical components in life support devices or systems without express written approval of Weforsemi.